



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

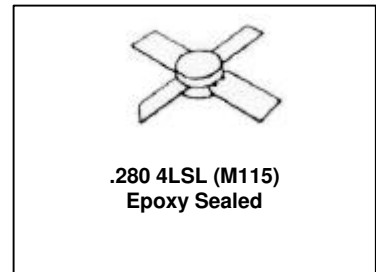


MS2206

**RF & MICROWAVE TRANSISTORS
AVIONICS APPLICATIONS**

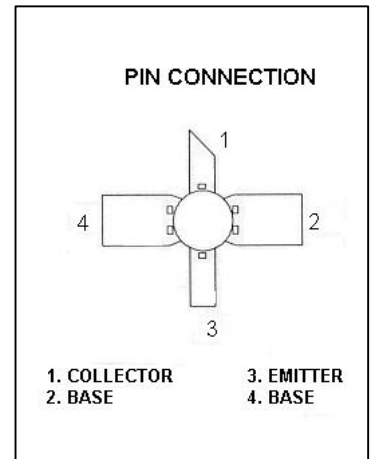
Features

- 1025-1150 MHz
- GOLD METALLIZATION
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- Pout = 4 W MINIMUM
- G_p= 10 dB
- COMMON BASE CONFIGURATION



DESCRIPTION:

The MS2206 is a common base, silicon NPN microwave transistor designed for Class C driver applications under DME or IFF pulse conditions. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation	7.5	W
V _{CE}	Collector-Emitter Bias Voltage	37	V
T _J	Junction Temperature	200	°C
I _C	Device Current	1.0	A
T _{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance*	35	°C/W
----------------------	-----------------------------------	----	------

ELECTRICAL SPECIFICATIONS (T_{case} = 25 °C)
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	I_C = 1 mA	I_E = 0 mA	45	---	---	V
BV_{CEO}	I_C = 5 mA	I_B = 0mA	20	---	---	V
BV_{EBO}	I_E = 1.0 mA	I_C = 0 mA	3.5	---	---	V
I_{CES}	V_{CE} = 35 V		---	---	1.0	mA
HFE	V_{CE} = 5 V	I_C = 100 mA	20	---	120	---

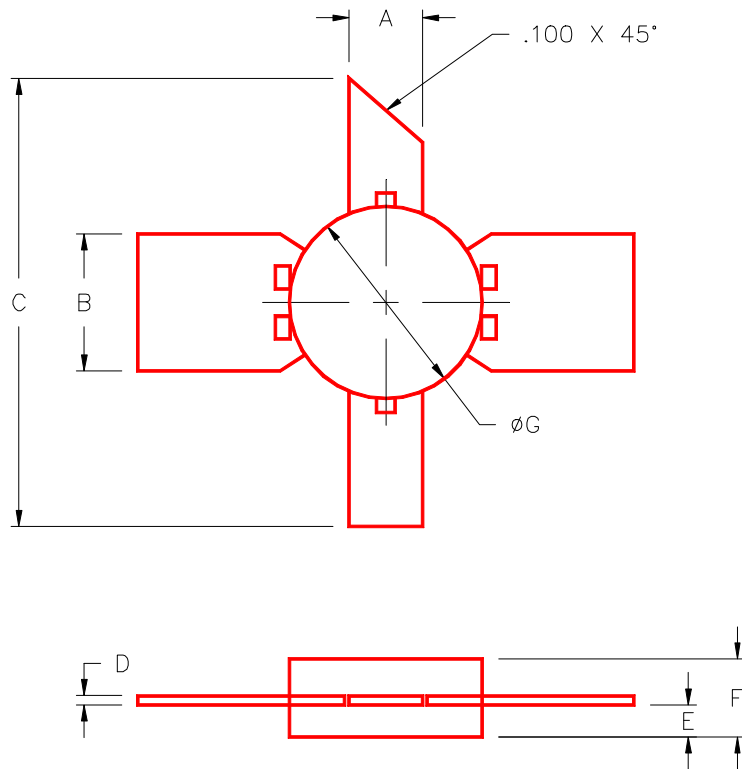
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 1025 - 1150 MHz	P_{IN} = 400mW	V_{CE} = 35V	4	---	---	W
G_p	f = 1025 - 1150 MHz	P_{IN} = 400mW	V_{CE} = 35V	10	---	---	dB

Conditions: Pulse Width = 10 μs Duty Cycle = 1%

PACKAGE MECHANICAL DATA

PACKAGE STYLE M115



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.095/2,41	.105/2,67			
B	.195/4,95	.205/5,21			
C	1.000/25,40				
D	.004/0,10	.007/0,18			
E	.050/1,27	.065/1,65			
F	.120/3,05	.135/3,43			
G	.275/6,99	.285/7,21			